

## Low Phase Noise CMOS XO (48MHz to 100MHz)

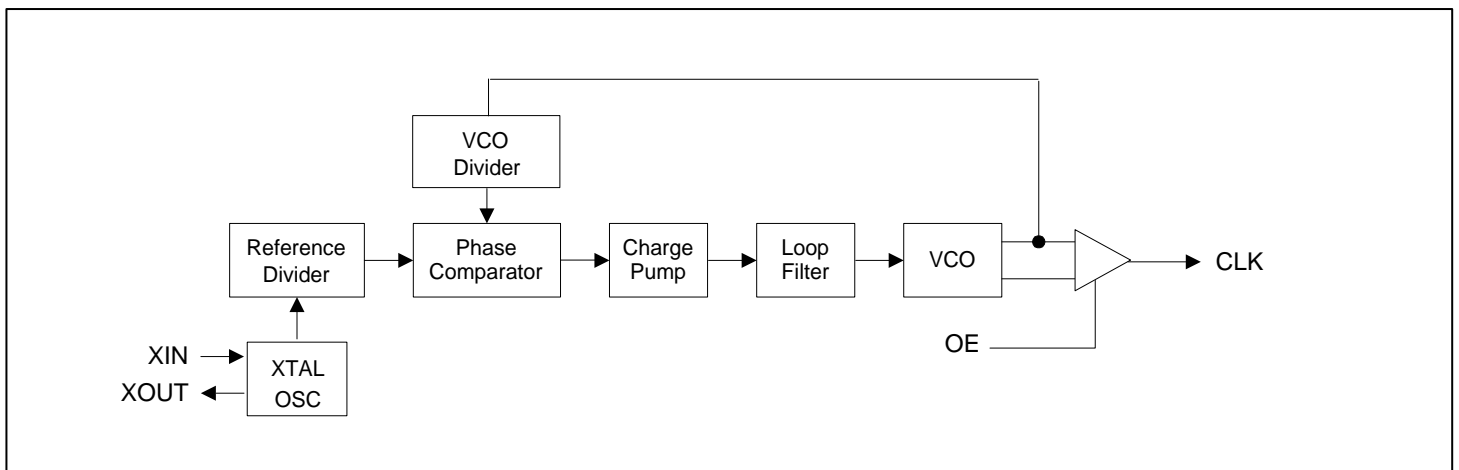
### FEATURES

- Low phase noise XO output for the 48MHz to 100MHz range (-130 dBc at 10kHz offset).
- 12 to 25MHz crystal input.
- Integrated crystal load capacitor: no external load capacitor required.
- Low jitter (RMS): 3ps period jitter (1 sigma).
- Selectable High Drive (30mA) or Standard Drive (10mA) output.
- 3.3V operation.
- Available in 8-Pin TSSOP or SOIC.

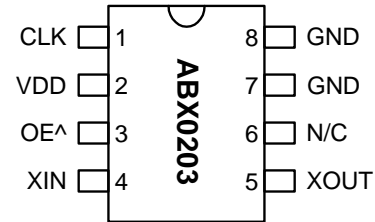
### DESCRIPTION

The ABX0203 is a low cost, high performance and low phase noise XO, providing less than -130dBc at 10kHz offset in the 48MHz to 100MHz operating range. The very low jitter (3ps RMS period jitter) makes this chip ideal for applications requiring clean reference frequency sources. Input crystal can range from 12 to 25MHz (fundamental resonant mode).

### BLOCK DIAGRAM



### PIN CONFIGURATION



Note: ^ denotes internal pull up

### OUTPUT RANGE

MULTIPLIER	FREQUENCY RANGE	OUTPUT BUFFER
X4	48 - 100MHz	CMOS

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### PIN DESCRIPTIONS

Name	Number	Type	Description
CLK	1	O	Output clock.
VDD	2	P	power supply.
OE	3	I	Output enable input. Disables (tri-state) output when low. Internal pull-up enables output by default if pin is not connected to low.
XIN	4	I	Crystal input. See Crystal Specification on page 3.
XOUT	5	I	Crystal output. See Crystal Specification on page 3.
N/C	6	-	Not connected.
GND	7, 8	P	Ground.

### ELECTRICAL SPECIFICATIONS

#### 1. Absolute Maximum Ratings

PARAMETERS	SYMBOL	MIN.	MAX.	UNITS
Supply Voltage	$V_{DD}$		4.6	V
Input Voltage, dc	$V_I$	-0.5	$V_{DD}+0.5$	V
Output Voltage, dc	$V_O$	-0.5	$V_{DD}+0.5$	V
Storage Temperature	$T_S$	-65	150	°C
Ambient Operating Temperature*	$T_A$	-40	85	°C
Junction Temperature	$T_J$		125	°C
Lead Temperature (soldering, 10s)			260	°C
ESD Protection, Human Body Model			2	kV

Exposure of the device under conditions beyond the limits specified by Maximum Ratings for extended periods may cause permanent damage to the device and affect product reliability. These conditions represent a stress rating only, and functional operations of the device at these or any other conditions above the operational limits noted in this specification is not implied.

\* Note: Operating Temperature is guaranteed by design for all parts (COMMERCIAL and INDUSTRIAL), but tested for COMMERCIAL grade only.

#### 2. DC Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Supply Current, Dynamic, with Loaded Outputs	$I_{DD}$	$F_{XIN} = 12 - 25\text{MHz}$ Output load of 10pF		16	20	mA
Operating Voltage	$V_{DD}$		2.97		3.63	V
Output drive current (High Drive)	$I_{OH}$	$V_{OH} = V_{DD}-0.4\text{V}, V_{DD}=3.3\text{V}$	30			mA
	$I_{OL}$	$V_{OL} = 0.4\text{V}, V_{DD} = 3.3\text{V}$	30			mA
Output drive current (Standard Drive)	$I_{OH}$	$V_{OH} = V_{DD}-0.4\text{V}, V_{DD}=3.3\text{V}$	10			mA
	$I_{OL}$	$V_{OL} = 0.4\text{V}, V_{DD} = 3.3\text{V}$	10			mA
Short Circuit Current				±50		mA

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### 3. AC Specifications

PARAMETERS	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Crystal Frequency			12		25	MHz
Output Clock Rise/Fall Time (Standard Drive)		0.3V ~ 3.0V with 15 pF load		2.4		ns
Output Clock Rise/Fall Time (High Drive)				1.2		
Output Clock Duty Cycle		Measured @ 50% V <sub>DD</sub>	45	50	55	%

### 4. Jitter and Phase Noise Specification

PARAMETERS	CONDITIONS	MIN.	TYP.	MAX.	UNITS
RMS Period Jitter (1 sigma – 1000 samples)	at 80MHz, with capacitive decoupling between V <sub>DD</sub> and GND.		3.5		ps
Phase Noise relative to carrier	80MHz @100Hz offset		-103		dBc/Hz
Phase Noise relative to carrier	80MHz @1kHz offset		-122		dBc/Hz
Phase Noise relative to carrier	80MHz @10kHz offset		-130		dBc/Hz
Phase Noise relative to carrier	80MHz @100kHz offset		-125		dBc/Hz

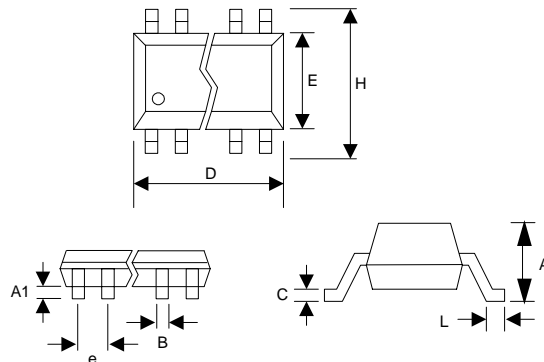
### 5. Crystal Specifications

PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Crystal Resonator Frequency	F <sub>XIN</sub>	12		25	MHz
Crystal Loading Capacitance Rating	C <sub>L</sub> (xtal)		20		pF
Driving power			1		mW
ESR	R <sub>s</sub>			30	Ω

## PACKAGE INFORMATION

8 PIN ( dimensions in mm )

Symbol	Narrow SOIC		TSSOP	
	Min.	Max.	Min.	Max.
A	1.47	1.73	-	1.20
A1	0.10	0.25	0.05	0.15
B	0.33	0.51	0.19	0.30
C	0.19	0.25	0.09	0.20
D	4.80	4.95	2.90	3.10
E	3.80	4.00	4.30	4.50
H	5.80	6.20	6.20	6.60
L	0.38	1.27	0.45	0.75
e	1.27 BSC		0.65 BSC	



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### ORDERING INFORMATION

*For part ordering, please contact our Sales Department:*

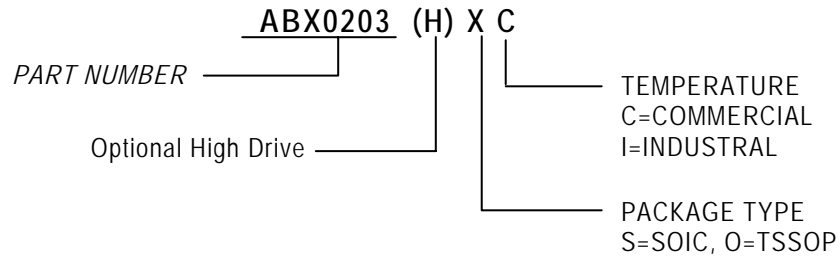
30332 Esperanza., Rancho Santa Margarita, Ca 92688

Ph: 949-546-8000 Fax: 949-546-8001

#### PART NUMBER

The order number for this device is a combination of the following:

Device number, Package type and Operating temperature range



<u>Order Number</u>	<u>Marking</u>	<u>Package Option</u>
ABX0203OC-T	ABX0203OC	TSSOP - Tape and Reel
ABX0203OC	ABX0203OC	TSSOP - Tube
ABX0203HOC-T	ABX0203HOC	TSSOP - Tape and Reel
ABX0203HOC	ABX0203HOC	TSSOP - Tube
ABX0203SC-T	ABX0203SC	SOIC - Tape and Reel
ABX0203SC	ABX0203SC	SOIC - Tube
ABX0203HSC-T	ABX0203HSC	SOIC - Tape and Reel
ABX0203HSC	ABX0203HSC	SOIC - Tube

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